

isc Silicon NPN Power Transistor

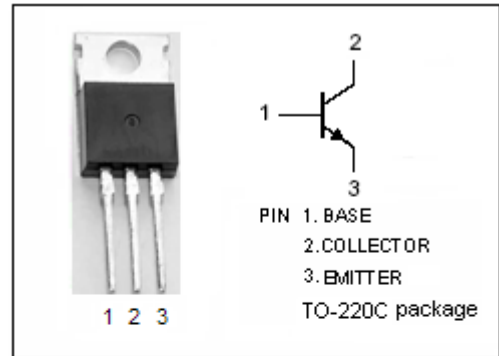
2SD569

DESCRIPTION

- High Collector Current: $I_C = 7A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.5V(Max) @ I_C = 5A$
- Complement to Type 2SB708

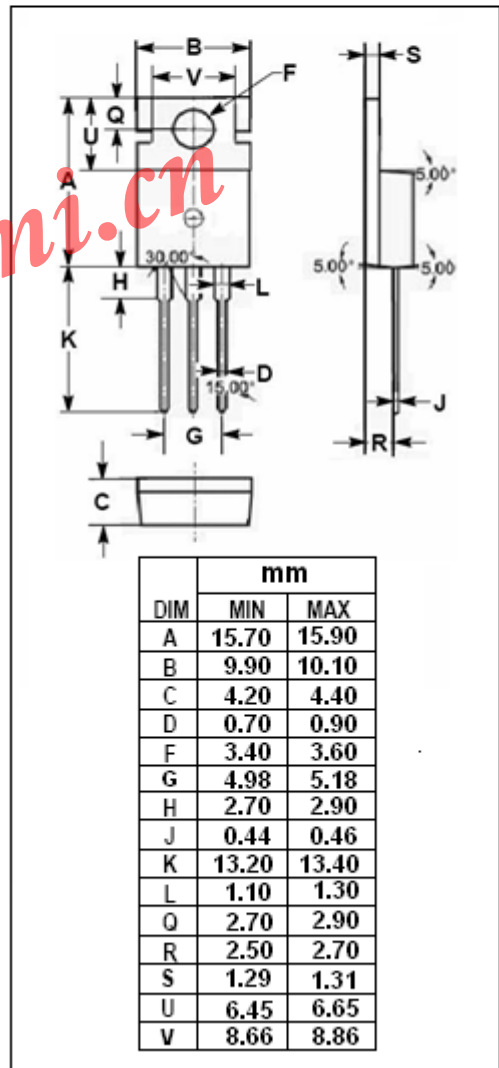
APPLICATIONS

- Designed for low-frequency power amplifiers and low-speed switching applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current-Continuous	3.5	A
P_C	Total Power Dissipation @ $T_C=25^{\circ}C$	40	W
	Total Power Dissipation @ $T_a=25^{\circ}C$	2	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SD569****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=3\text{A}; V_{CE}=1\text{V}$	40		200	
h_{FE-2}	DC Current Gain	$I_C=5\text{A}; V_{CE}=1\text{V}$	20			

◆ h_{FE-1} Classifications

M	L	K
40-80	60-120	100-200